

IN THE CLAIMS

Claims 1-5 (cancelled).

6. (original) An integrated circuit comprising a semiconductor substrate and a nonvolatile memory cell having an active area formed in the semiconductor substrate, the memory cell comprising:

a dielectric on the active area; and

a floating gate on the dielectric, the floating gate having a horizontal top surface projecting laterally beyond the active area.

7. (original) The integrated circuit of Claim 6 wherein at a location at which the top surface of the floating gate projects beyond the active area, the floating gate has a sidewall, and at least a top portion of the sidewall extends laterally outward and beyond the active area as the sidewall is traced upward.

8. (original) The integrated circuit of Claim 7 further comprising a dielectric region abutting said top portion of the sidewall.

9. (original) An integrated circuit comprising a semiconductor substrate and a nonvolatile memory cell having an active area formed in the semiconductor substrate, the memory cell comprising:

a dielectric on the active area; and

a floating gate on the dielectric, wherein the floating gate has a sidewall, and at least a top portion of the sidewall extends laterally outward as the sidewall is traced upward.

10. (original) The integrated circuit of Claim 9 further comprising a dielectric region physically contacting, and extending along, said top portion of the sidewall.

Any questions regarding this case can be addressed to the undersigned at 408-392-9250.

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